

STB40100C SCHOTTKY RECTIFIER

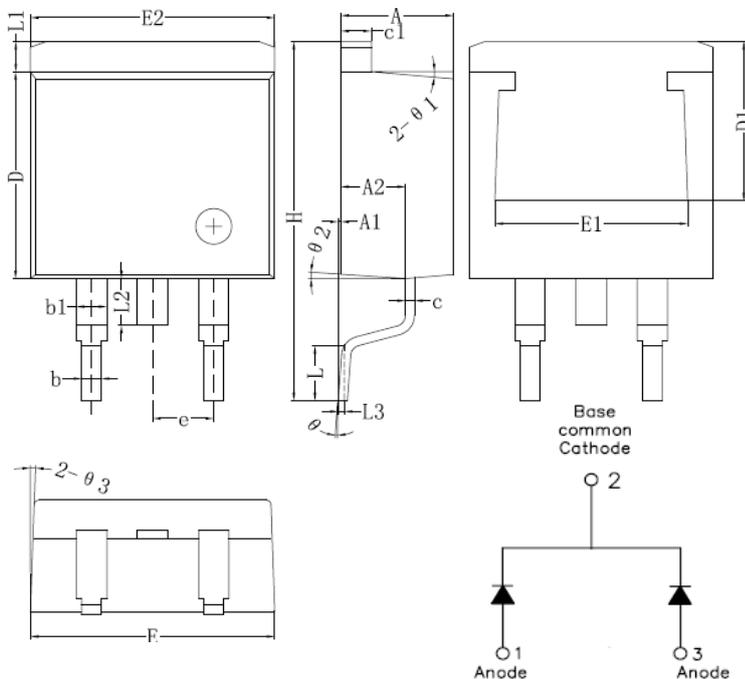
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 150 °C T_J operation
- Center tap configuration
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

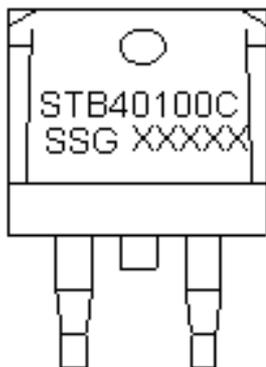
Mechanical Dimensions: In mm



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
c1	1.17	1.27	1.37
D	8.55	8.70	8.85
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.18
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.70
L1	1.17	1.27	1.40
L2			2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

D² PAK

Marking Diagram:



Where XXXXX is YYWWL

- S = Device Type
- T = Ultralow VF
- B = Package type
- 40 = Forward Current (40A)
- 100 = Reverse Voltage (100V)
- C = Configuration
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
STB40100C	D ² PAK (Pb-Free)	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C=105\text{ }^\circ\text{C}$ rectangular wave form	40	A
Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	300	A



Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (per leg)*	V _{F1}	@ 5A, Pulse, T _J = 25 °C	0.47	-	V
		@ 10A, Pulse, T _J = 25 °C	0.54	-	
@ 20A, Pulse, T _J = 25 °C		0.68	0.75		
	V _{F2}	@ 5A, Pulse, T _J = 125 °C	0.38	-	V
		@ 10A, Pulse, T _J = 125 °C	0.51	-	
		@ 20A, Pulse, T _J = 125 °C	0.64	0.70	
Reverse Current at DC condition (per leg)	I _{R1}	@V _R = 70V, T _J = 25 °C @V _R = 100V, T _J = 25 °C	0.012 0.030	- 1	mA
Reverse Current (per leg) *	I _{R2}	@V _R = 70V, T _J = 125 °C @V _R = 100V, T _J = 125 °C	10 15	- 75	mA
Junction Capacitance (per leg)	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	845	-	pF

* Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T _J	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case (per leg)	R _{θJC}	DC operation	2.0	°C/W
Approximate Weight	wt	-	1.85	g
Case Style	D ² PAK			

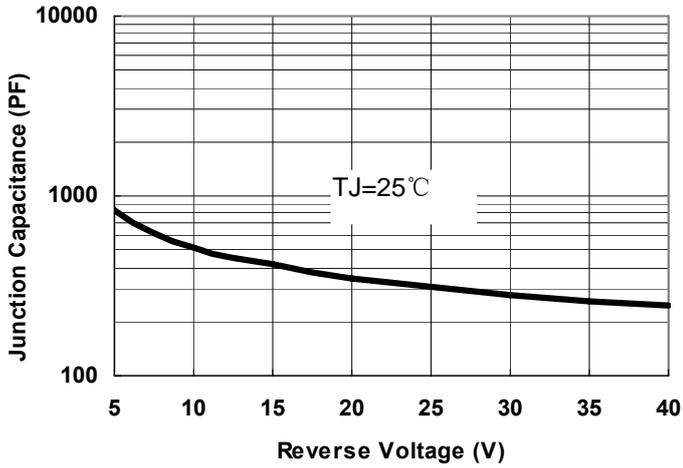


Fig.1-Typical Junction Capacitance

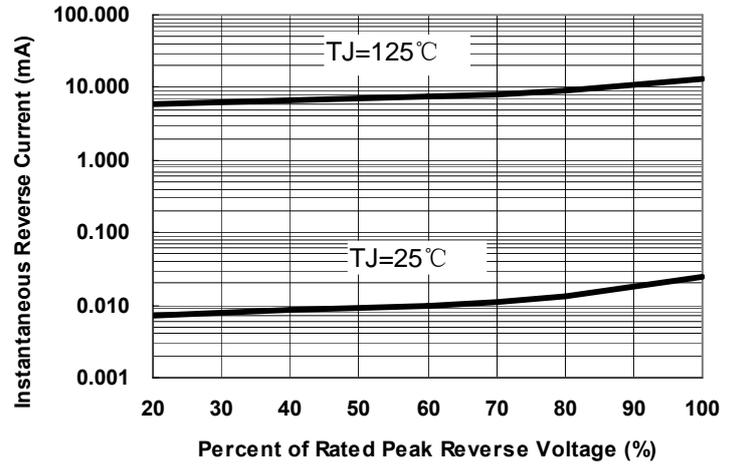


Fig.2-Typical Reverse Characteristics

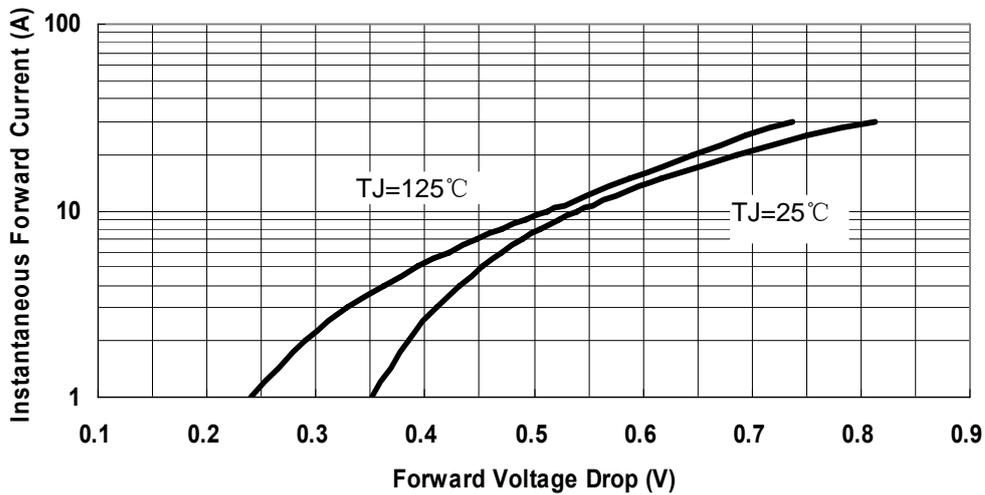


Fig.3-Typical Instantaneous Forward Voltage Characteristics



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